DISCRETE SEMICONDUCTORS

DATA SHEET

PDTC143E series NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Product data sheet Supersedes data of 2004 Mar 18 2004 Aug 05



NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
R1	bias resistor	4.7	-	kΩ
R2	bias resistor	4.7	_	kΩ

DESCRIPTION

NPN resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACE	(AGE	MARKING CODE(1)	PNP COMPLEMENT	
ITPE NUMBER	PHILIPS EIAJ		WARKING CODE	PNP COMPLEMENT	
PDTC143EE	SOT416	SC-75	02	PDTA143EE	
PDTC143EEF	SOT490	SC-89	51	PDTA143EEF	
PDTC143EK	SOT346	SC-59	02	PDTA143EK	
PDTC143EM	SOT883	SC-101	E1	PDTA143EM	
PDTC143ES	SOT54 (TO-92)	SC-43	TC143E	PDTA143ES	
PDTC143ET	SOT23	-	*02	PDTA143ET	
PDTC143EU	SOT323	SC-70	*02	PDTA143EU	

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CVMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTC143ES	1 R1 R2 3 MAM364	1 2 3	base collector emitter
PDTC143EE PDTC143EEF PDTC143EK PDTC143ET PDTC143EU	Top view Top view Top view Top view	1 2 3	base emitter collector
PDTC143EM	2 R1 R2 2 bottom view MHC506	1 2 3	base emitter collector

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE							
TYPE NUMBER	NAME	DESCRIPTION	VERSION					
PDTC143EE	_	plastic surface mounted package; 3 leads	SOT416					
PDTC143EEF	_	plastic surface mounted package; 3 leads	SOT490					
PDTC143EK	_	plastic surface mounted package; 3 leads	SOT346					
PDTC143EM	_	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm	SOT883					
PDTC143ES	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54					
PDTC143ET	_	plastic surface mounted package; 3 leads	SOT23					
PDTC143EU	_	plastic surface mounted package; 3 leads	SOT323					

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
collector-base voltage	open emitter	_	50	V
collector-emitter voltage	open base	_	50	V
emitter-base voltage	open collector	_	10	V
input voltage				
positive		_	+30	V
negative		_	-10	V
output current (DC)		_	100	mA
peak collector current		_	100	mA
total power dissipation	T _{amb} ≤ 25 °C			
SOT54	note 1	_	500	mW
SOT23	note 1	_	250	mW
SOT346	note 1	_	250	mW
SOT323	note 1	_	200	mW
SOT416	note 1	_	150	mW
SOT883	notes 2 and 3	_	250	mW
SOT490	notes 1 and 2	_	250	mW
storage temperature		-65	+150	°C
junction temperature		_	150	°C
operating ambient temperature		-65	+150	°C
	collector-base voltage collector-emitter voltage emitter-base voltage input voltage positive negative output current (DC) peak collector current total power dissipation SOT54 SOT23 SOT346 SOT323 SOT416 SOT883 SOT490 storage temperature junction temperature	collector-base voltage collector-emitter voltage emitter-base voltage input voltage positive negative output current (DC) peak collector current total power dissipation SOT34 SOT346 SOT323 SOT346 SOT323 SOT416 SOT883 SOT490 storage temperature junction temperature	collector-base voltage open emitter - collector-emitter voltage open base - emitter-base voltage open collector - input voltage positive negative output current (DC) peak collector current total power dissipation T _{amb} ≤ 25 °C - SOT54 note 1 - SOT23 note 1 - SOT346 note 1 - SOT323 note 1 - SOT346 note 1 - SOT383 note 1 - SOT883 notes 2 and 3 - SOT490 notes 1 and 2 - storage temperature -65 junction temperature -	collector-base voltage open emitter - 50 collector-emitter voltage open base - 50 emitter-base voltage open collector - 10 input voltage - +30 - positive - - -10 output current (DC) - 100 - 100 peak collector current - 100 - 100 - 100 total power dissipation T _{amb} ≤ 25 °C - - 500 - 500 - 500 - 500 - 250 - 500 - 250 - 500 - 250 - 250 - 250 - 250 - 250 - 250 - 250 - 250 - 250 - 250 - 250 - 250 - - 250 - - 250 - - - - - -

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT883	notes 2 and 3	500	K/W
	SOT490	notes 1 and 2	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	_	_	900	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	30	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 100 \mu A; V_{CE} = 5 V$	_	1.1	0.5	V
$V_{i(on)}$	input-on voltage	$I_C = 20 \text{ mA}; V_{CE} = 0.3 \text{ V}$	2.5	1.9	_	V
R1	input resistor		3.3	4.7	6.1	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	-	_	2.5	pF

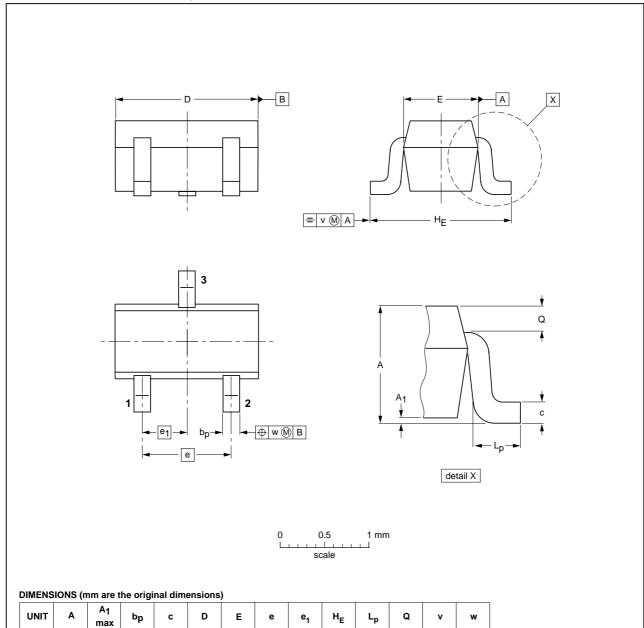
NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

PACKAGE OUTLINES



SOT416



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT416			SC-75		04-11-04 06-03-16

1.75

1.45

0.45

0.23

0.2

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0.30

0.25

0.10

0.9

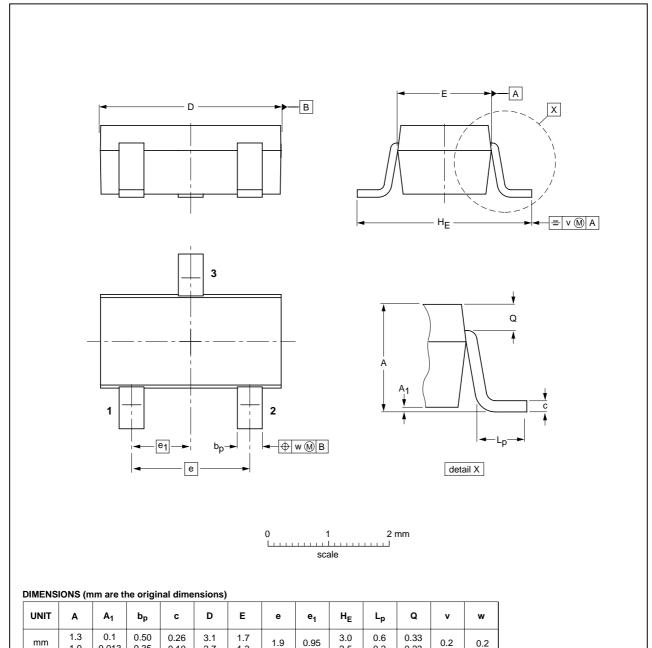
0.95

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

Plastic surface-mounted package; 3 leads

SOT346



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59A		04-11-11 06-03-16	

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1.0

0.013

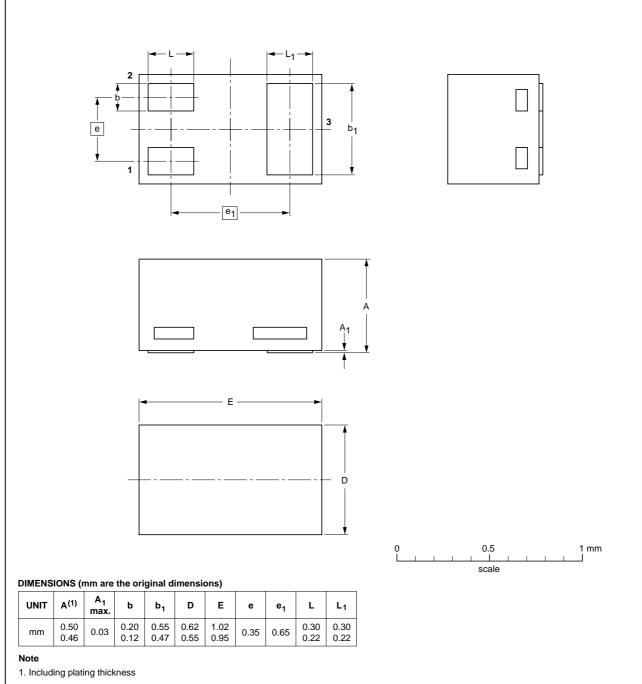
0.35

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



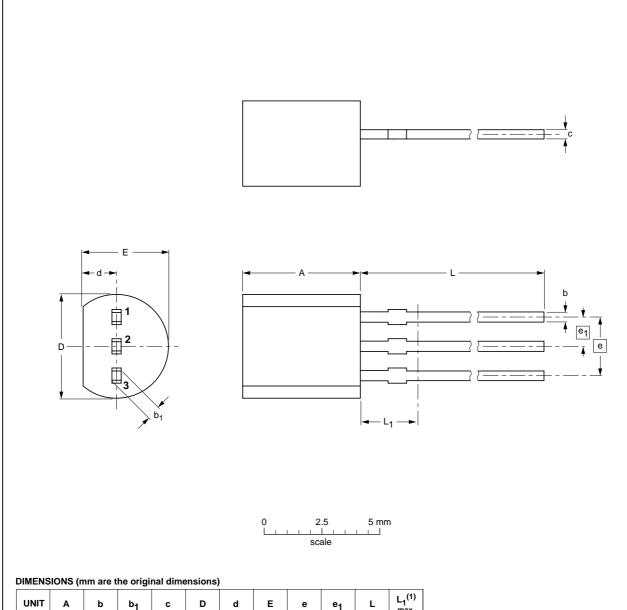
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VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT883			SC-101		03-02-05 03-04-03	

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

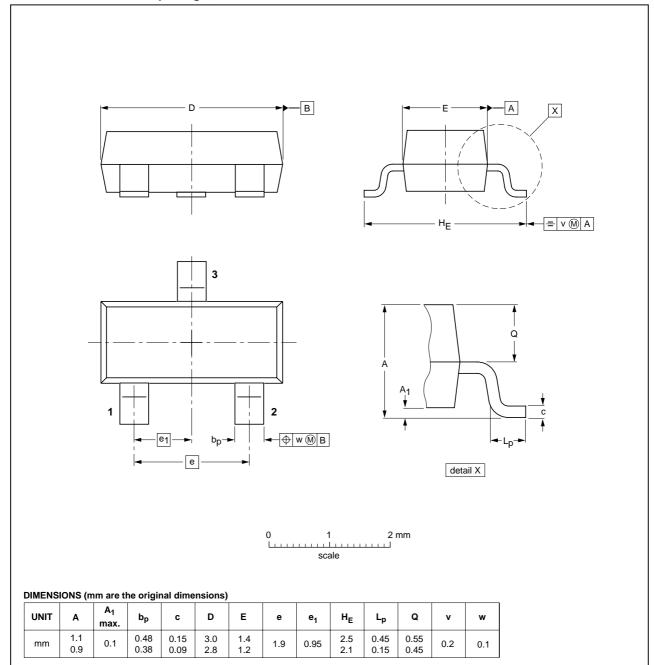
JEDEC	JEITA	PROJECTION	ISSUE DATE
TO-92	SC-43A		04-06-28 04-11-16

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

Plastic surface-mounted package; 3 leads

SOT23



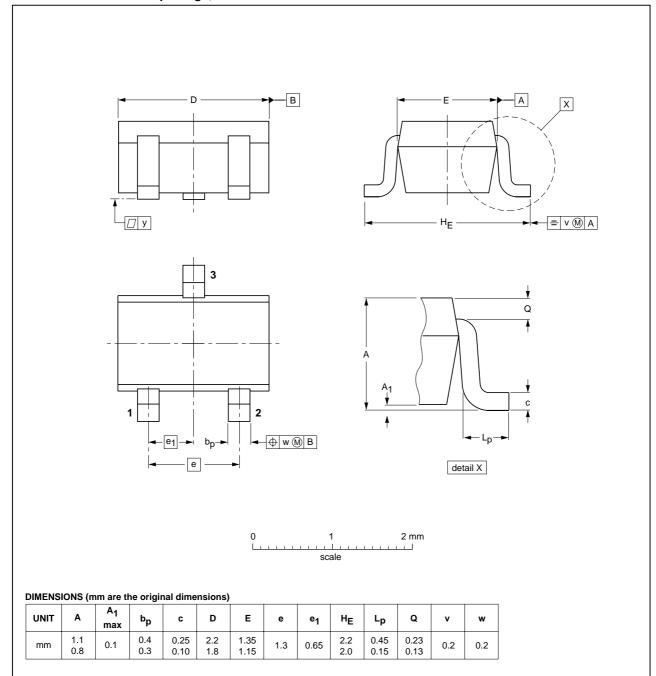
OUTLINE			RENCES		ISSUE DATE
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	TO-236AB				-04-11-04 06-03-16
-	IEC	IEC JEDEC		IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

Plastic surface-mounted package; 3 leads

SOT323



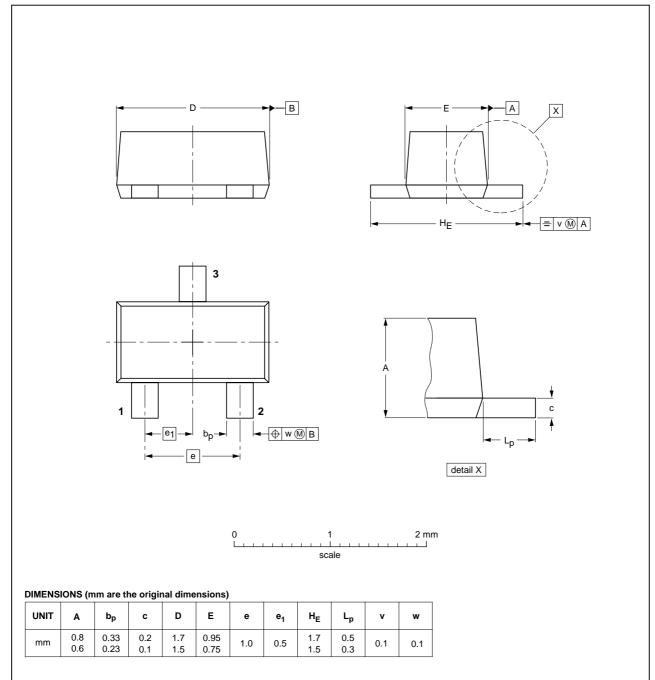
OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT323			SC-70			-04-11-04 06-03-16

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

Plastic surface-mounted package; 3 leads

SOT490



OUTLINE	NE REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT490			SC-89		05-07-28 06-03-16

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTC143E series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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